

## Electronic Acknowledgement Receipt

<b>EFS ID:</b>	8349595
<b>Application Number:</b>	10565621
<b>International Application Number:</b>	
<b>Confirmation Number:</b>	2319
<b>Title of Invention:</b>	Stacked structure and production method thereof
<b>First Named Inventor/Applicant Name:</b>	Hubert Moriceau
<b>Customer Number:</b>	90678
<b>Filer:</b>	Jasper W. Dockrey/Christine Pisarski
<b>Filer Authorized By:</b>	Jasper W. Dockrey
<b>Attorney Docket Number:</b>	9905-37 (BIF116044/US)
<b>Receipt Date:</b>	03-SEP-2010
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<b>Time Stamp:</b>	17:00:50
<b>Application Type:</b>	U.S. National Stage under 35 USC 371

### Payment information:

Submitted with Payment	no
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### File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	Foreign Reference	RU-1282757.pdf	215504 <small>9b0986e97e97e07e02e0a441d4f136d5875f720c</small>	no	7

**Warnings:**

**Information:**

2	Foreign Reference	WO-9520824A1.pdf	852361 3a088a48f171338a3d416458cfcc070c26d7	no	24
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3	Foreign Reference	WO-9908316.pdf	724323 83c08c01812a26c673bdc5150b3cc0234eaf5d5	no	22
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4	Foreign Reference	WO-9935674A1.pdf	1786999 44517133a9d904a99b9c81e13c0a78cfd9ba	no	44
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5	Foreign Reference	WO-9939378.pdf	1169894 2b426d9a390d10aa77b0af30c79465eeef48717	no	31
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6	Foreign Reference	WO-0048238A1.pdf	2047387 9d232ede54e514803d796c3504b4f9933eb6d81	no	55
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8	Foreign Reference	WO-0111930A2.pdf	1637080 ce943a0b74072a1ee5ac2d8427e9f726953d53	no	42
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9	Foreign Reference	WO-0143168A2.pdf	1163934 8135dc788c95a0d386c1b6428794b94ef2529d	no	31
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10	Foreign Reference	WO-0205344A1.PDF	1241265 080d2ed8c349993b62a680463881c17b37bd88	no	30
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11	Foreign Reference	WO-0247156A1.pdf	1004413 dc2672bdcdb6da1873e843223a285e1977cafa	no	28
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14	NPL Documents	Agarwal-Aditya-Efficient-Production-of-Silicon.pdf	332510 b88d7292e1e7bc88059a63b128d7e92385d8888	no	2
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17	NPL Documents	Ascheron-C-et-al-A-Comparative-Study.pdf	805187 ac0b6d8b99d8d6f07d797996ac2a8715a5d53	no	10
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21	NPL Documents	Ascheron-C-et-al-Proton-Beam-Modification.pdf	1335819 78478b8dc445c70c7b0d5b4f75c284c81b6b26	no	23
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24	NPL Documents	Ascheron-C-et-al-The-Effect-of-Hydrogen-Implantation-Induced-Stress.pdf	514211 ee6c9495151ac79ab2c0e2d1c0f80e0529ba017	no	10
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25	NPL Documents	Aspar_et_al_Smart_Cut_The_basic_fabrication_process_UNIBOND.pdf	462907 411623027adeck4124b4bd1c82f9495c9e03b	no	10
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26	NPL Documents	Aspar_et_al_US_App_No_09-77516_allowed_claims.pdf	112185 0214672cedd104ac57a9d947c3899a501f692c6	no	3
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27	NPL Documents	Aspar_B_Basic_Mechanisms_involved_in_the_Smart_Cut_Process.pdf	440138 54297a0a98bd913c1f8c3ec73057f12b3a0d	no	8
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29	NPL Documents	Aspar_B_et_al_Transfer_of_Structured_and_Patterned_Thin.pdf	80682 4807811e307ed1c1cd19a9c3196a481c6b54e9f	no	2
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38	NPL Documents	Bruel_Michel_Application_of_Hydrogen_on_Beams_to_Silicon.pdf	483916 dd52908bc824ccc32f962cd44748958e6538b3d	no	7
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42	NPL Documents	Bruel_M_Smart_Cut_A_New_SOI_Material_Technology.pdf	2170085 2b80c4b136c26ab8c7e76750e971fb71c5865c	no	25
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46	NPL Documents	Canham_et_al_Radiative_Recombination_Channels_Due_to_Hydrogen.pdf	217996 ea035d8ee042c438b2a72a79f043c50294f2808	no	5
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47	NPL Documents	Carter-et-al-Applications-of-Ion-Beams-To-Materials.PDF	600857 2313e45396c07c38808802d5f5bdc24782a6a2	no	13
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48	NPL Documents	Carter_G_et_al_The_Collection_of_Ions_Implanted_in_Semiconductors_II.pdf	669972 31894788490c3b661b568056821eaf518c315b5408	no	8
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51	NPL Documents	Cerofolini_et_al_Ultradense_Gas_Bubbles_in_Hydrogen-or-Helium-Implanted_or_Co-Implanted_Silicon.pdf	510141 f702e15a9b8a7e7b62d78e0de8bd7e7c54894c5a	no	7
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52	NPL Documents	Cerofolini-GF_Hydrogen_and_Helium_Bubbles_1.PDF	2728185 d2d59f31db4822832a78eb3dbf999539d5dc08ad	no	52
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53	NPL Documents	Chu_WK_et_al_Radiation_Damage_of_50-250_keV_Hydrogen.pdf	663443 5d5f78c209a8bdc9dc0db796a79e918a513d19a15	no	10
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54	NPL Documents	Chu_Ion-Implantation_In_Semiconductors.PDF	499300 99886882ac68544495f7105450147a8f055958ec	no	12
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58	NPL Documents	Csepregi_L_et_al_Regrowth_Behavior_of_Inon-Implanted_Amorphous_Layers_on_111_Silicon.pdf	125356 c3c7818d324711113b47404ec2fac0d61a7f33	no	2
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59	NPL Documents	Cullis_AG_et_al_Comparative_Study_of_Annealed_Neon-argon.pdf	660281 26c7d16dd122616d512140258ced0dd0ff6a18	no	11
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Total Files Size (in bytes):			45684769		
<p>This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.</p> <p><b><u>New Applications Under 35 U.S.C. 111</u></b></p> <p>If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.</p> <p><b><u>National Stage of an International Application under 35 U.S.C. 371</u></b></p> <p>If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.</p> <p><b><u>New International Application Filed with the USPTO as a Receiving Office</u></b></p> <p>If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.</p>					